

Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

LDTB143EET1G

- **Applications**
Inverter, Interface, Driver

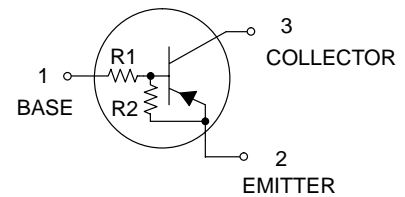
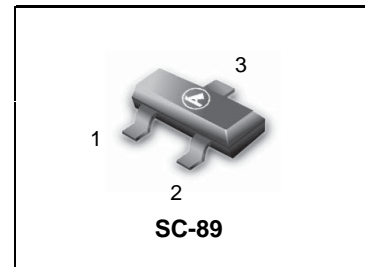
- **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on / off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.

- **Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	-50	V
Input voltage	V _{IN}	-30 to +10	V
Output current	I _C	-500	mA
Power dissipation	P _D	200	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



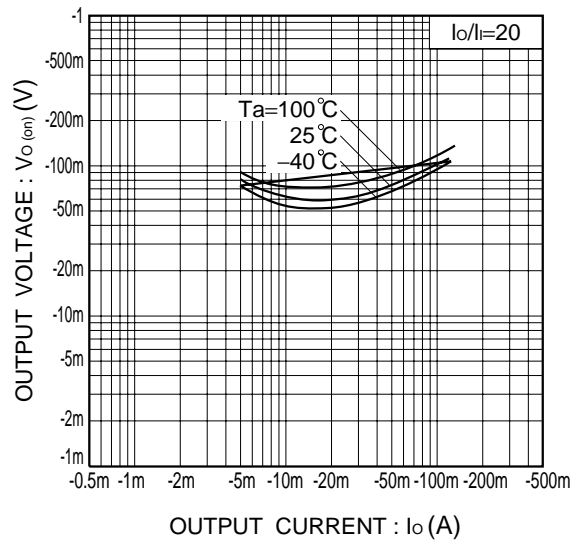
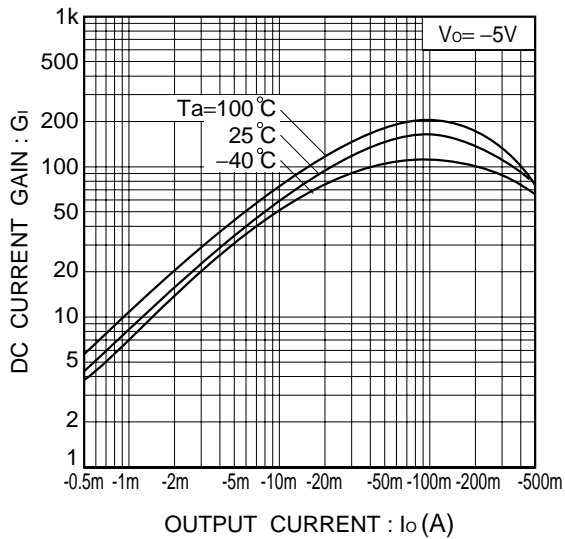
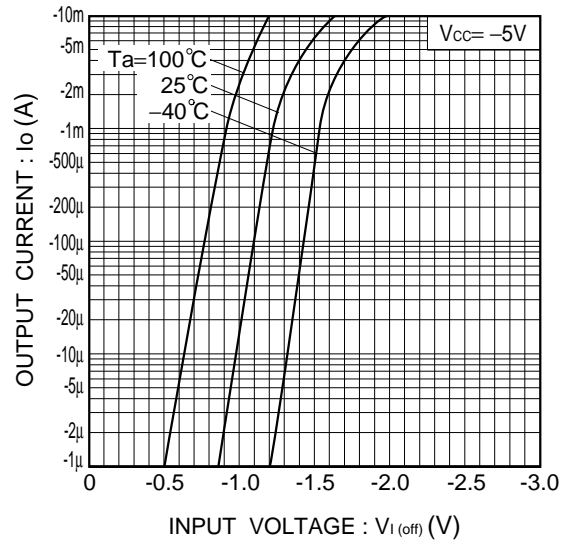
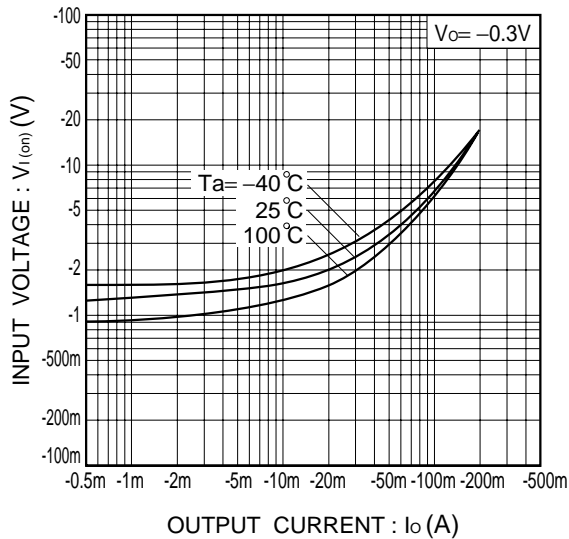
DEVICE MARKING AND RESISTOR VALUES

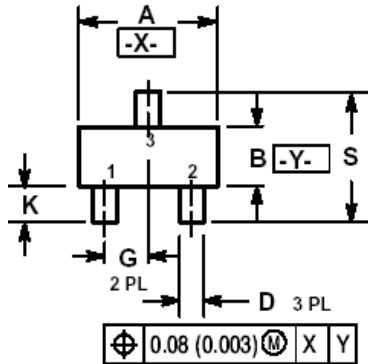
Device	Marking	R1 (K)	R2 (K)	Shipping
LDTB143EET1G	K6	4.7	4.7	3000/Tape & Reel
LDTB143EET3G	K9	4.7	4.7	10000/Tape & Reel

- **Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{I(off)}	-	-	-0.5	V	V _{CC} = -5V, I _C = -100μA
	V _{I(on)}	-3	-	-	V	V _O = -0.3V, I _C = -20mA
Output voltage	V _{O(on)}	-	-0.1	-0.3	V	I _O /I _E = -50mA/-2.5mA
Input current	I _I	-	-	-1.8	mA	V _I = -5V
Output current	I _{O(off)}	-	-	-0.5	μA	V _{CC} = -50V, V _I =0V
DC current gain	G _I	47	-	-	-	V _O = -5V, I _C = -50mA
Input resistance	R ₁	3.29	4.7	6.11	kΩ	-
Resistance ratio	R ₂ /R ₁	0.8	1	1.2	-	-
Transition frequency	f _T *	-	200	-	MHz	V _{CE} = -10V, I _E =50mA, f=100MHz

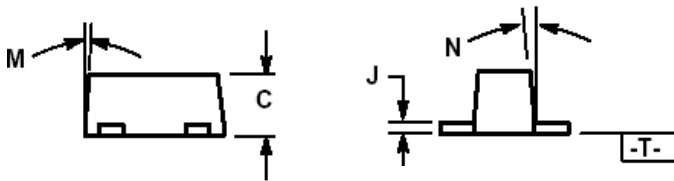
* Characteristics of built-in transistor

LDTB143EET1G
●Electrical characteristic curves


LDTB143EET1G
SC-89


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067

